

electrons emitted by said current emitter,

B1
cont. said current emitter comprising a treated current emission surface having a reduced atomic concentration of oxygen resulting from treatment of the current emission surface with a plasma enhanced chemical vapor deposition hydrogenation process followed by a nitrogen infusion process.

Please replace claim 15 with the following rewritten claim 15:

B2 15. (Amended) The device according to claim 13, wherein said current emitter has a base on said barrier layer and a projecting top connected with said base.

Please replace claim 18 with the following rewritten claim 18:

B3 18. (Amended) The device according to claim 12, wherein said current emitter comprises sides and a tip, said sides being surrounded by an insulating layer to prevent current from radiating out of the sides, wherein said sides do not include any portion of the tip.

Please add the following new claims 24 and 25:

24. (New) A field emission display device comprising:

B4 at least one current emitter formed of a doped silicon; and
a substrate having a phosphor coating on at least a portion of the substrate, said